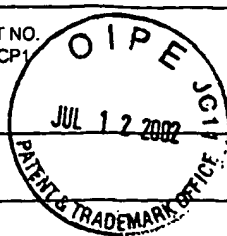


FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.196CP1	APPLICATION NO. 09/318,073
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Zhu, et al.	GROUP 2826
		FILING DATE May 25, 1999	



U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)	
W	US 2001/0030886 A1	10/18/01	Thewes, et al.				
W	US 2001/0050859 A1	12/13/01	Schwarzl				

FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	

MSO-3132.DOC:afa
070802

EXAMINER	DATE CONSIDERED
EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
MICRON.196CP1APPLICATION NO.
09/318,073INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Zhu, et al.FILING DATE
May 25, 1999GROUP
2826

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
NO	5,661,062	8/26/97	Prinz			
	5,861,328	1/19/99	Tehrani et al.			
	5,902,690	5/11/99	Tracy et al.			
	5,940,319	8/17/99	Durlam et al.			Aug. 31, 1998
	5,956,267	9/21/99	Hurst et al.			Dec. 18, 1997
	6,048,739	4/11/00	Hurst et al.			Dec. 18, 1997
	6,165,803	12/26/00	Chen et al.			May 17, 1999
	6,510,078 B2	01/21/03	Schwarzl			
W	6,580,636 B2	06/17/03	Thewes et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
W	JP 2000 090658 A	3/31/00	Japan (Abstract)			X	

EXAMINER
INITIAL

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

W	Prinz, "Magnetoelectronics", Science Magazine, Vol. 282, Nov. 27, 1998.
	Wang et al., Feasibility of Ultra-Dense Spin-Tunneling Random Access Memory, IEEE Transactions on Magnetism, Vol. 33, No. 6, Nov. 1997.
	Lee, Chih-Ling, "A Study of Magnetoresistance Random-Access Memory," date unknown
W	Kaakani, H. "NON-VOLATILE MEMORY (MRAM) ANXXX," [online], Honeywell, March 1999 [retrieved on November 19, 2001]. Retrieved from the Internet: <URL: www.ssec.honeywell.com/avionics/h_gmr.pdf>

L:\DOCS\MSO\MSO-5499.DOC
032304

EXAMINER

DATE CONSIDERED

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.